



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

SOT-89-3L Plastic-Encapsulate Transistors

PXT8050 TRANSISTOR (NPN)

FEATURES

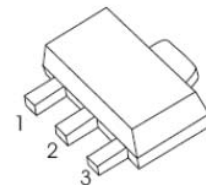
- Compliment to PXT8550

MARKING: Y1

MAXIMUM RATINGS ($T_a=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	40	V
V_{CEO}	Collector-Emitter Voltage	25	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current -Continuous	1.5	A
P_C	Collector Power dissipation	0.5	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-55~150	$^\circ\text{C}$

SOT-89-3L



1. BASE
2. COLLECTOR
3. EMITTER

ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu\text{A}$, $I_E=0$	40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=0.1\text{mA}$, $I_B=0$	25			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu\text{A}$, $I_C=0$	5			V
Collector cut-off current	I_{CBO}	$V_{CB}=40\text{V}$, $I_E=0$			0.1	μA
Emitter cut-off current	I_{CEO}	$V_{CE}=20\text{V}$, $I_E=0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=5\text{V}$, $I_C=0$			0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=1\text{V}$, $I_C=100\text{mA}$	85		400	
	$h_{FE(2)}$	$V_{CE}=1\text{V}$, $I_C=800\text{mA}$	40			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=800\text{mA}$, $I_B=80\text{mA}$			0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=800\text{mA}$, $I_B=80\text{mA}$			1.2	V
Base-emitter voltage	V_{BE}	$V_{CE}=1\text{V}$, $I_C=10\text{mA}$			1	V
Base-emitter positive favor voltage	V_{BEF}	$I_B=1\text{A}$			1.55	V
Transition frequency	f_T	$V_{CE}=10\text{V}$, $I_C=50\text{mA}$, $f=30\text{MHz}$	100			MHz
output capacitance	C_{ob}	$V_{CB}=10\text{V}$, $I_E=0$, $f=1\text{MHz}$			15	pF

CLASSIFICATION OF $h_{FE(1)}$

Rank	B	C	D	D3
Range	85-160	120-200	160-300	300-400

Typical Characteristics

PXT8050

